

A cross-sectional view of a device. A central vertical protrusion, labeled 22, extends from a top surface. At the base of this protrusion, there is a small, shaded rectangular region labeled 20. Below this region, the device splits into two symmetrical, bulbous internal chambers. The left chamber is labeled 14A at its upper part and 14B at its lower part. The right chamber is labeled 16A at its upper part and 16B at its lower part. A central vertical channel, labeled 28 with an arrow pointing upwards, runs through the middle of the device, connecting the top surface to the bottom. The bottom of the device is wider than the top.

A cross-sectional view of a semiconductor device. A central opening 28 is formed in a substrate 20. A central electrode 22 is positioned above the opening. The opening is flanked by two regions, 14A and 14B on the left, and 16A and 16B on the right. The regions 14A and 16A are the upper portions of the flanking regions, while 14B and 16B are the lower portions. The central electrode 22 is connected to the upper portion of the opening 28.

*FIG. 2B*

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